

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A method for manufacturing a semiconductor device includes ~~the steps of forming a first insulating film on a substrate, forming a second insulating film on the first insulating film, and forming a gate electrode on the second insulating film. The step of forming a~~ Forming the second insulating film has a first step of includes supplying film-forming materials and ~~making~~ adsorbing the film-forming materials ~~adsorbed~~ on the first insulating film, ~~a second step of purging the film-forming materials that has have not been adsorbed, a third step of supplying oxidants to oxidize the adsorbed film-forming materials, and a fourth step of purging the oxidants that has have not contributed to oxidization. The step of forming a~~ Forming the second insulating film is repeated for a plurality of in cycles, continuously, and the purging time in the fourth step of the oxidants in the an initial predetermined number of the cycles is made longer than the purging time in the fourth step of the oxidants in following cycles following the initial number of cycles.